



## MMBT2907ALT1

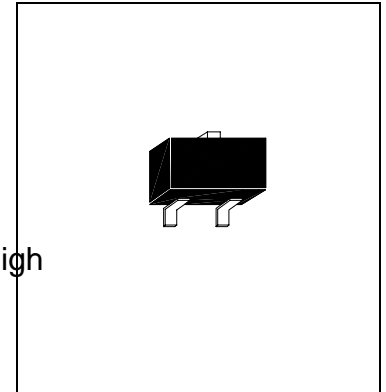
PNP EPITAXIAL PLANAR TRANSISTOR

### Description

The MMBT2907ALT1 is designed for general purpose amplifier and high-speed switching, medium power switching applications.

### Features

- Low Collector Saturation Voltage.
- High Speed Switching.
- For Complementary Use With NPN Type HMBT2222A.



### Absolute Maximum Ratings

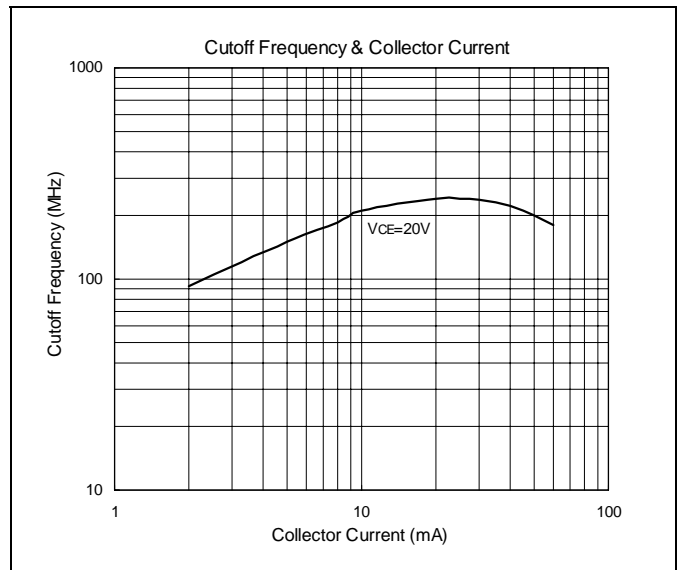
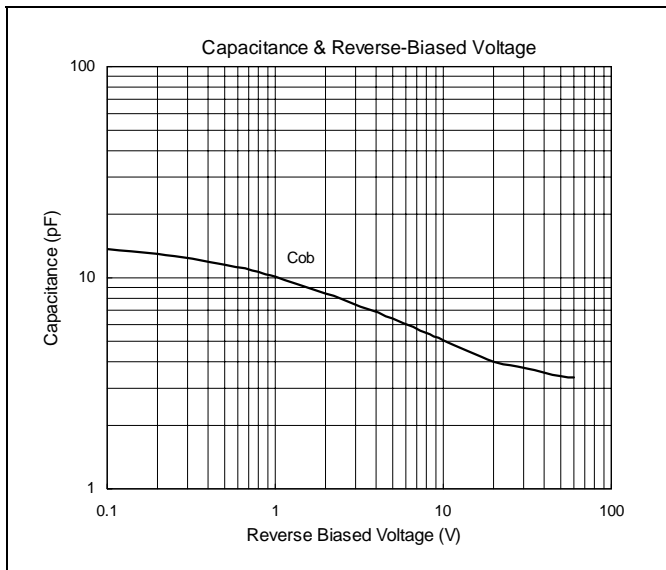
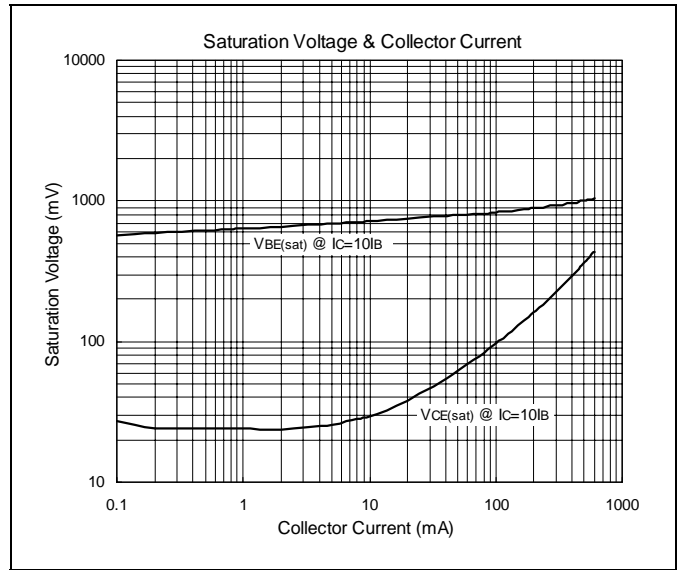
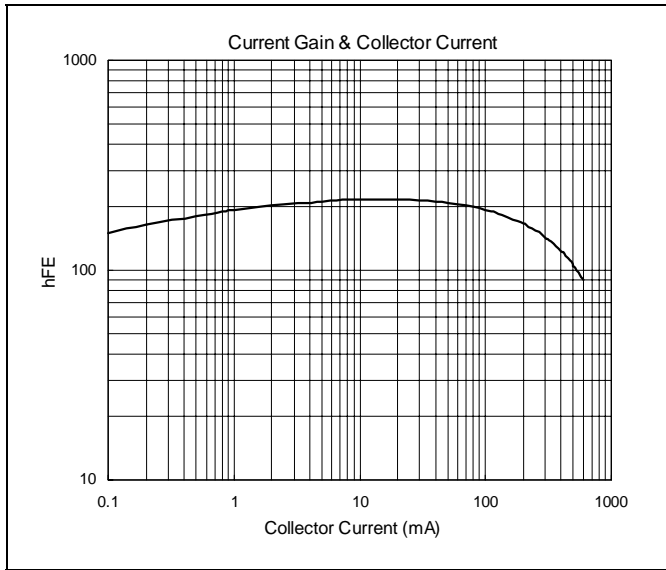
- Maximum Temperatures
  - Storage Temperature..... -55~+150°C
  - Junction Temperature..... +150°C
- Maximum Power Dissipation
  - Total Power Dissipation (Ta=25°C) ..... 250 mW
- Maximum Voltages and Currents (Ta=25°C)
  - VCBO Collector to Base Voltage ..... 60 V
  - VCEO Collector to Emitter Voltage ..... 60 V
  - VEBO Emitter to Base Voltage ..... 5 V
  - IC Collector Current ..... 600 mA

### Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=10uA
BVCEO	60	-	-	V	IC=10mA
BVEBO	5	-	-	V	IC=10uA
ICBO	-	-	10	nA	VCB=50V
ICEX	-	-	50	nA	VCE=30V, VBE=0.5V
VCE(sat)1	-	0.2	0.4	V	IC=150mA, IB=15mA
VCE(sat)2	-	0.5	1.6	V	IC=500mA, IB=50mA
VBE(sat)1	-	-	1.3	V	IC=150mA, IB=15mA
VBE(sat)2	-	-	2.6	V	IC=500mA, IB=50mA
hFE1	75	-	-		VCE=10V, IC=100uA
hFE2	100	-	-		VCE=10V, IC=1mA
hFE3	100	-	-		VCE=10V, IC=10mA
hFE4	100	180	300		VCE=10V, IC=150mA
hFE5	50	-	-		VCE=10V, IC=500mA
fT	200	-	-	MHz	VCB=20V, IC=50mA, f=100MHz
Cob	-	-	8	pF	VCB=10V, f=1MHz

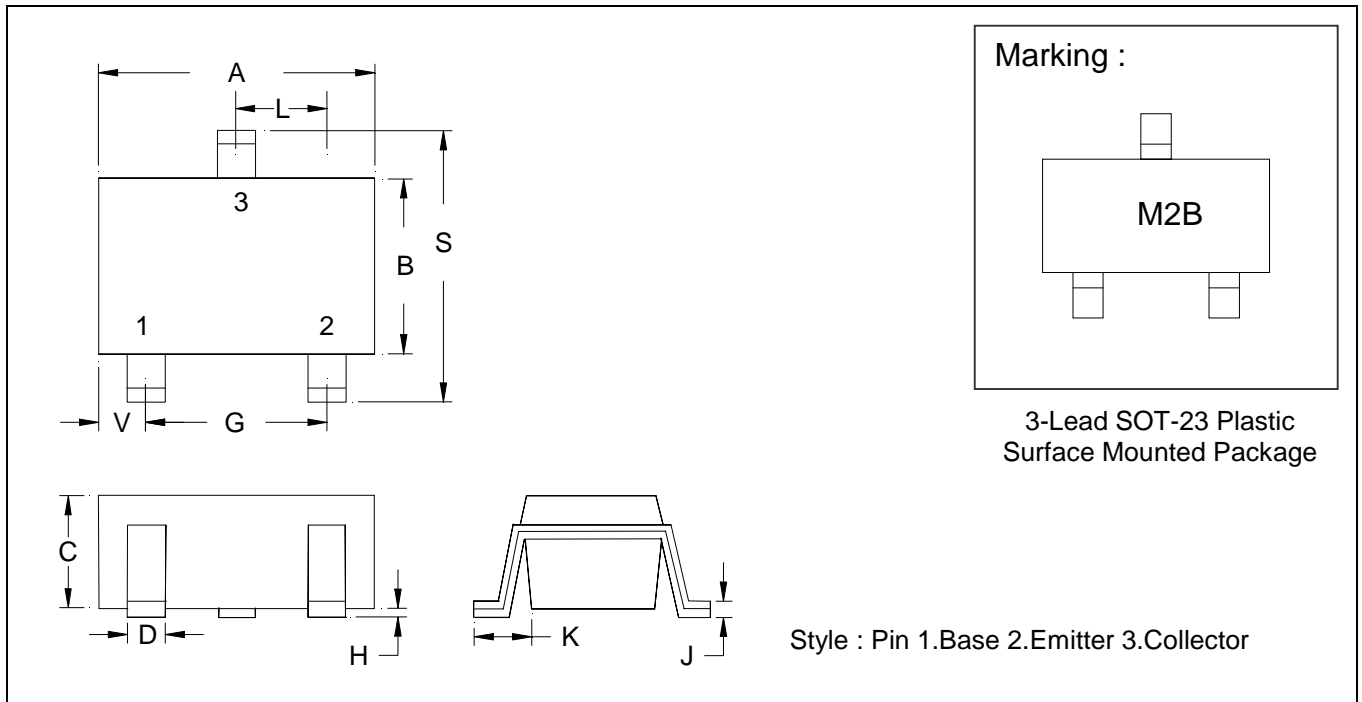


## Characteristics Curve





## SOT-23 Dimension



\*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.118	2.80	3.00	J	0.0035	0.0043	0.09	0.11
B	0.0550	0.0630	1.40	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0354	0.0512	0.90	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0886	0.1083	2.25	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	-	0.0040	-	0.10					